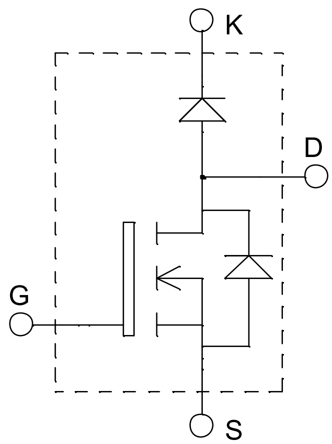
Microsemi
POWER PRODUCTS GROUP

APT10M11JVRU2

ISOTOP® Boost chopper MOSFET Power Module

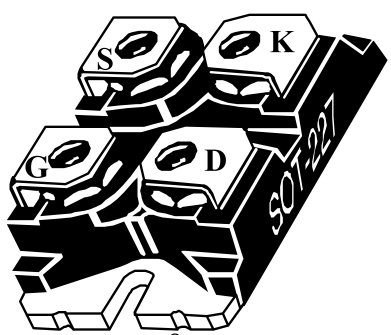
V_{DSS} = 100V
R_{DSon} = 11mΩ max @ Tj = 25°C
I_D = 142A @ Tc = 25°C



Application
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features
- Power MOS V® MOSFETs
  - Low R_{DSon}
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic diode
  - Avalanche energy rated
  - Very rugged
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very rugged
- Low profile
- RoHS Compliant



ISOTOP®

Absolute maximum ratings

Symbol	*Parameter*			*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage			100	V
I_D	Continuous Drain Current		T_c = 25°C	142	A
			T_c = 80°C	106	
I_{DM}	Pulsed Drain current			576	
V_{GS}	Gate - Source Voltage			±30	V
R_{DSon}	Drain - Source ON Resistance			11	mΩ
P_D	Maximum Power Dissipation		T_c = 25°C	450	W
I_{AR}	Avalanche current (repetitive and non repetitive)			144	A
E_{AR}	Repetitive Avalanche Energy			50	mJ
E_{AS}	Single Pulse Avalanche Energy			2500	
IF_{AV}	Maximum Average Forward Current	Duty cycle=0.5	Tc = 90°C	30	A
IF_{RMS}	RMS Forward Current (Square wave, 50% duty)			47	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 100V, T_j = 25°C			250	µA
		V_{GS} = 0V, V_{DS} = 80V, T_j = 125°C			1000	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 71A			11	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 2.5mA	2		4	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V			±100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		8600		pF
C_{oss}	Output Capacitance			3200		
C_{rss}	Reverse Transfer Capacitance			1180		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 50V I_D = 50A @ T_J=25°C		300		nC
Q_{gs}	Gate – Source Charge			95		
Q_{gd}	Gate – Drain Charge			110		
$T_{d(on)}$	Turn-on Delay Time	V_{GS} = 15V V_{Bus} = 50V I_D = 142A @ T_J=25°C R_G = 0.6Ω		16		ns
T_r	Rise Time			48		
$T_{d(off)}$	Turn-off Delay Time			51		
T_f	Fall Time			9		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode Forward Voltage	I_F = 30A		1.1	1.15	V
		I_F = 60A		1.4		
		I_F = 30A, T_j = 125°C		0.9		
I_{RM}	Maximum Reverse Leakage Current	V_R = 200V, T_j = 25°C			250	µA
		V_R = 200V, T_j = 125°C			500	
C_T	Junction Capacitance	V_R = 200V		94		pF
t_{rr}	Reverse Recovery Time	I_F=1A, V_R=30V, di/dt =200A/µs, T_j = 25°C		21		ns
	Reverse Recovery Time	I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 25°C		24		
		I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 125°C		48		
I_{RRM}	Maximum Reverse Recovery Current	I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 25°C		3		A
		I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 125°C		6		
Q_{rr}	Reverse Recovery Charge	I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 25°C		33		nC
		I_F = 30A, V_R = 133V, di/dt =200A/µs, T_j = 125°C		150		
t_{rr}	Reverse Recovery Time	I_F = 30A, V_R = 133V, di/dt =1000A/µs, T_j = 125°C		31		ns
Q_{rr}	Reverse Recovery Charge			335		nC
I_{RRM}	Maximum Reverse Recovery Current			19		A

Thermal and package characteristics

Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{thJC}	Junction to Case Thermal Resistance	MOSFET			0.28	°C/W
		Diode			1.21	
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz		2500			V
T_J,T_{STG}	Storage Temperature Range		-55		150	°C
T_L	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

Typical MOSFET Performance Curve

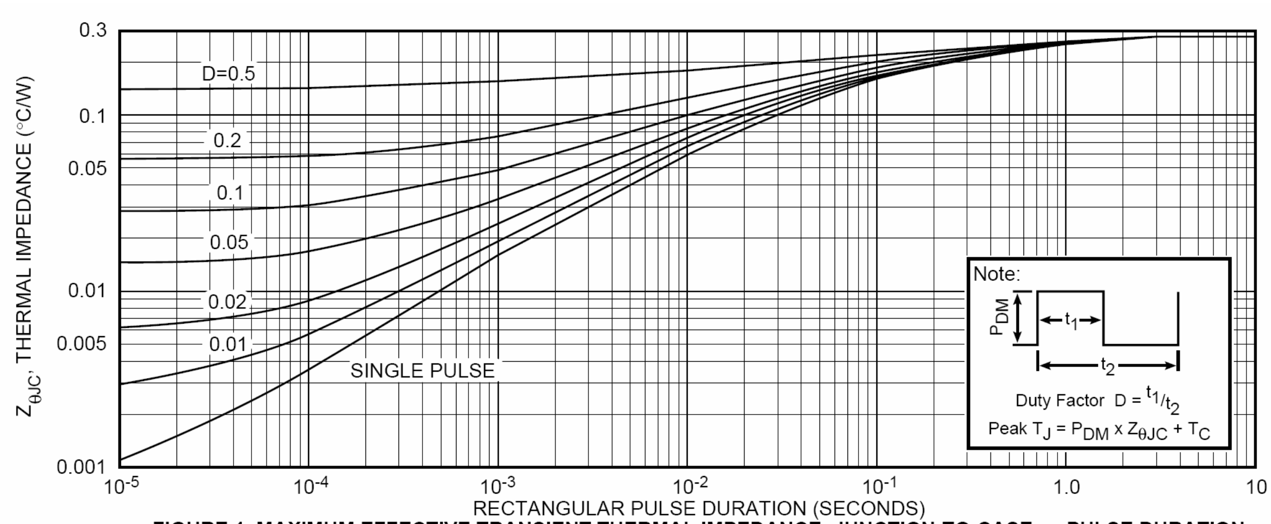


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

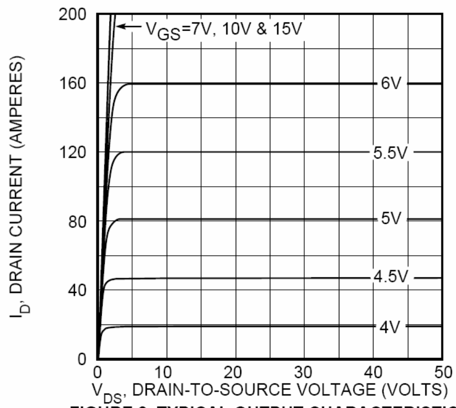


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

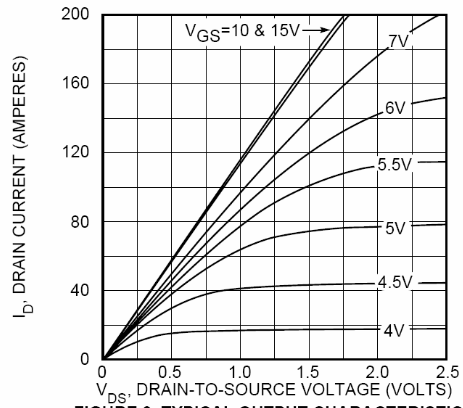


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

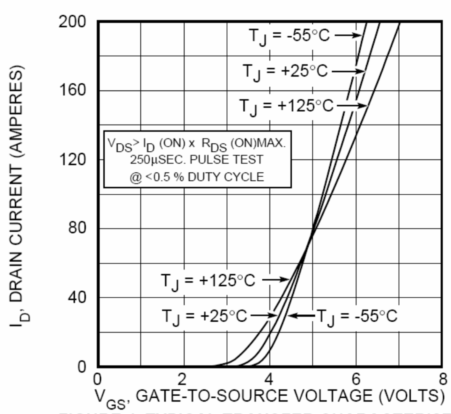


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

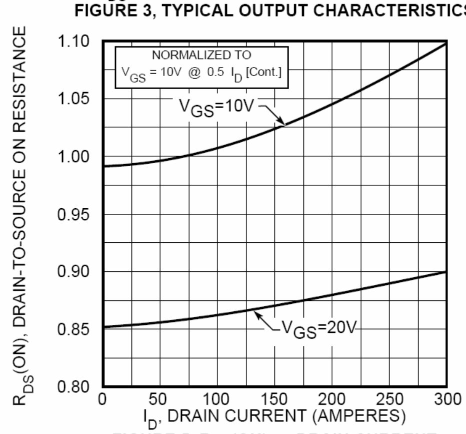


FIGURE 5, R_{DS}(ON) vs DRAIN CURRENT

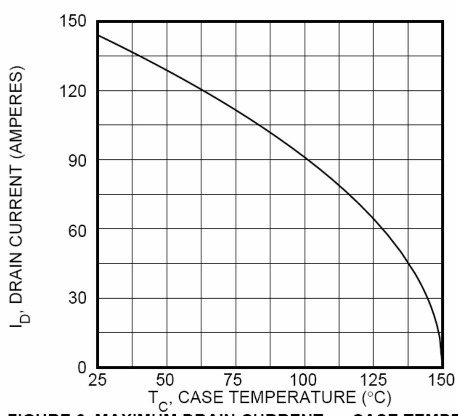


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

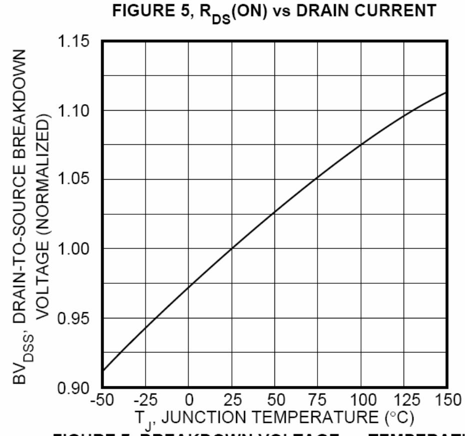


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

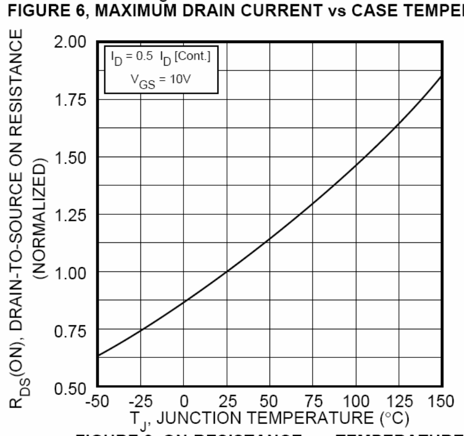


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

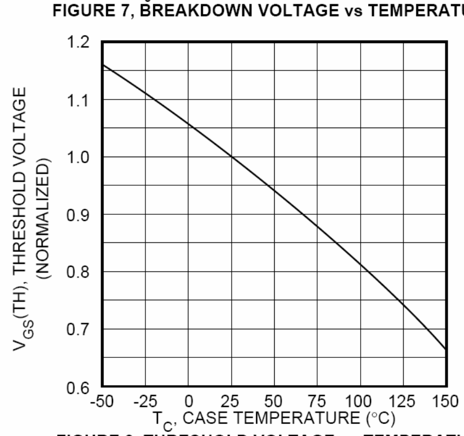


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

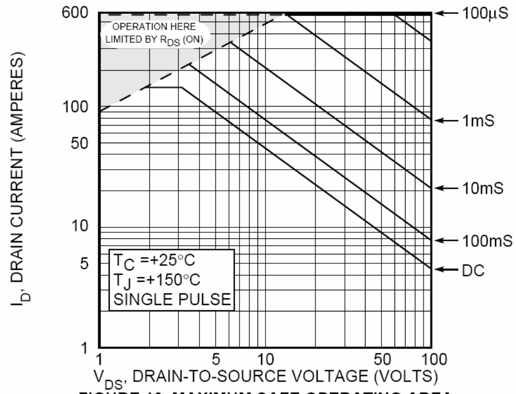


FIGURE 10, MAXIMUM SAFE OPERATING AREA

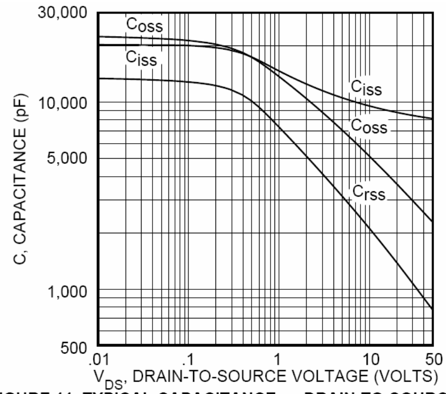


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

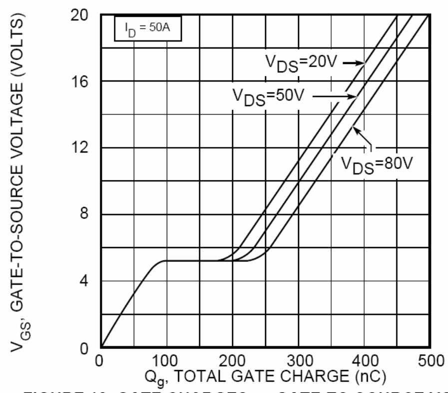


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

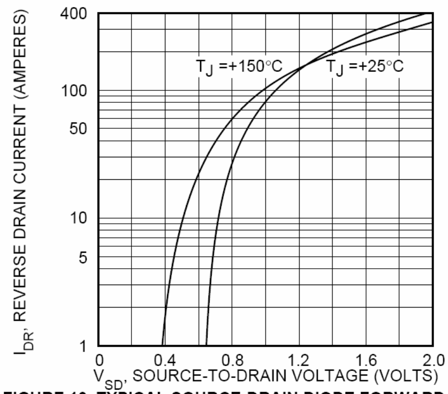


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

Typical Diode Performance Curve

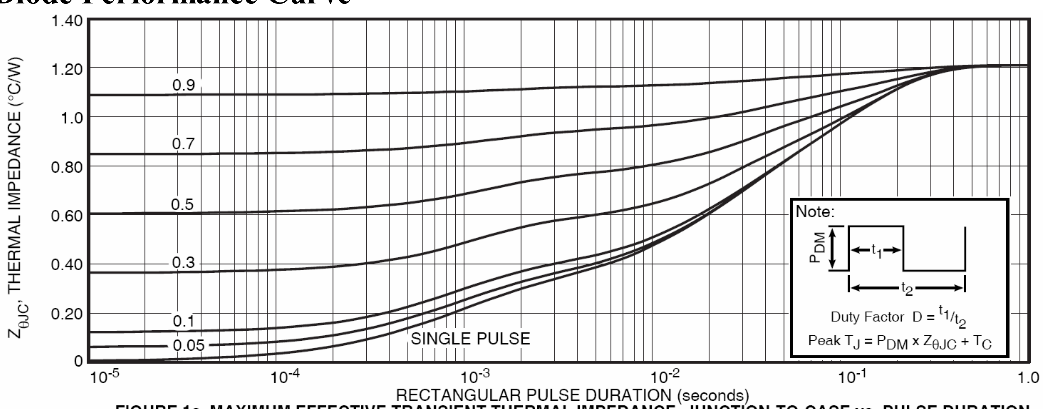


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

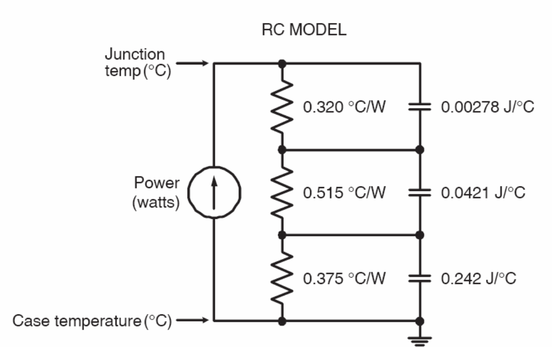


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

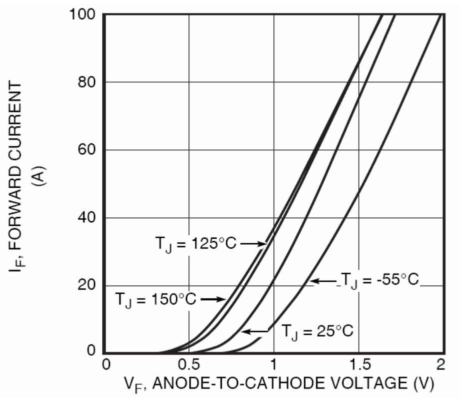


Figure 2. Forward Current *vs.* Forward Voltage

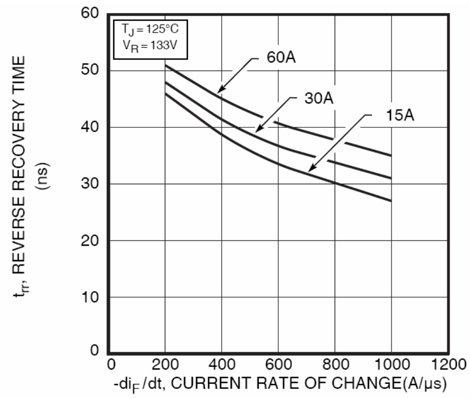


Figure 3. Reverse Recovery Time *vs.* Current Rate of Change

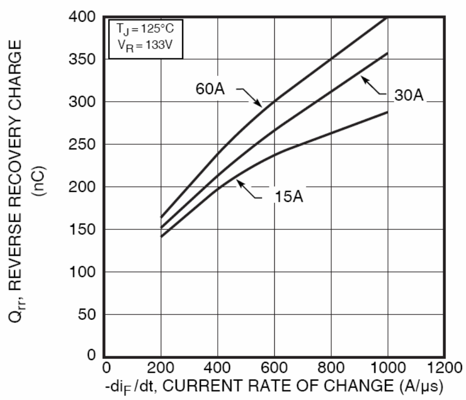


Figure 4. Reverse Recovery Charge *vs.* Current Rate of Change

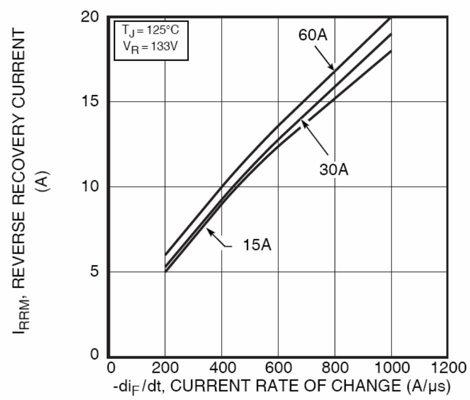


Figure 5. Reverse Recovery Current *vs.* Current Rate of Change

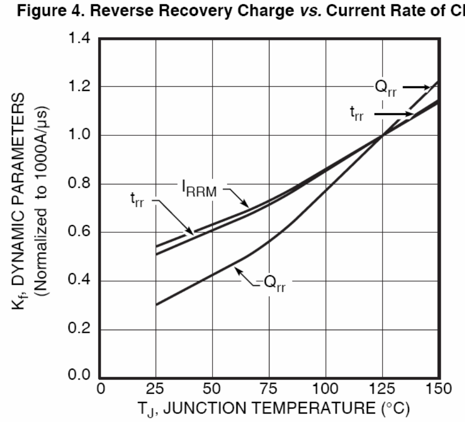


Figure 6. Dynamic Parameters *vs.* Junction Temperature

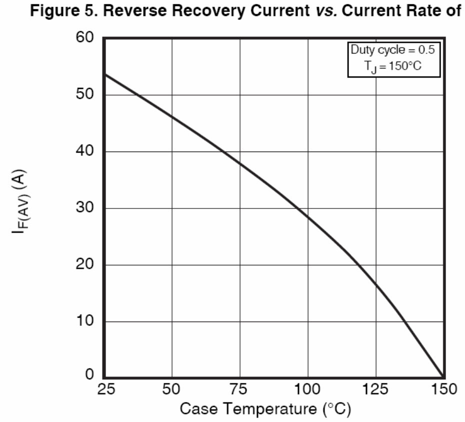


Figure 7. Maximum Average Forward Current *vs.* CaseTemperature

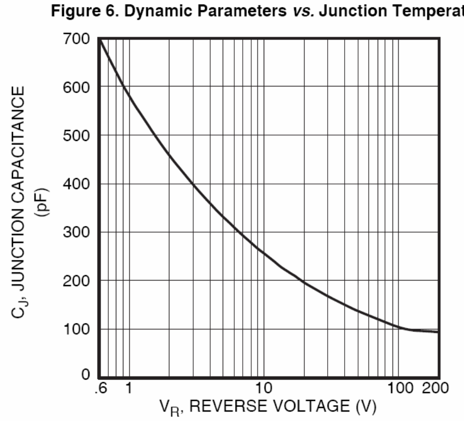


Figure 8. Junction Capacitance *vs.* Reverse Voltage

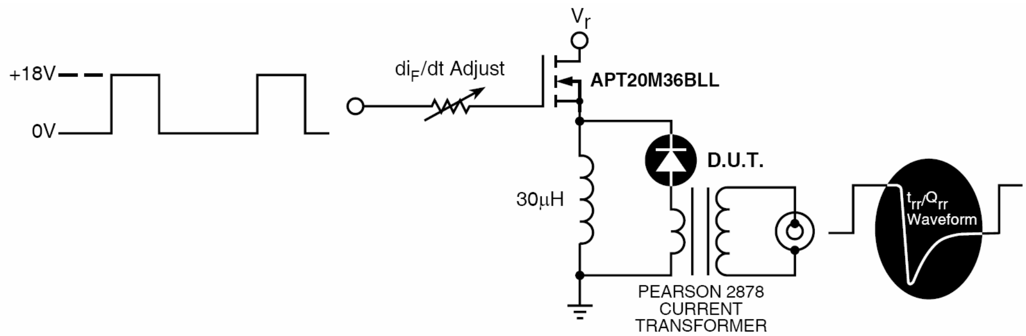


Figure 9. Diode Test Circuit

1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

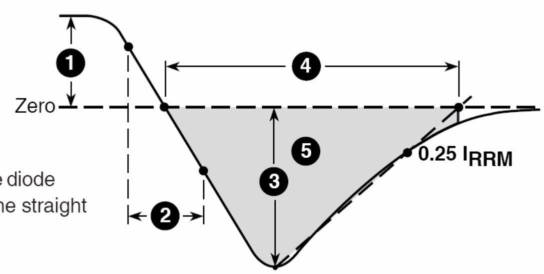
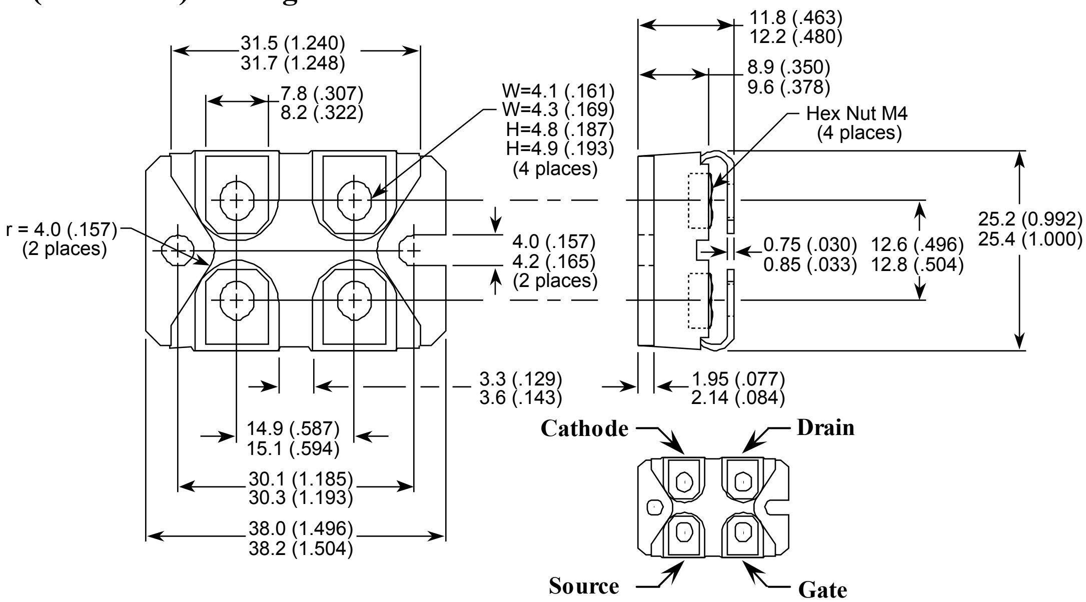


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

ISOTOP® is a registered trademark of ST Microelectronics NV

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending.

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- Консультации по применению компонента;
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- Техническая поддержка проекта;
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Как с нами связаться

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